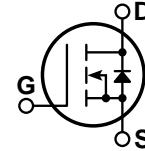
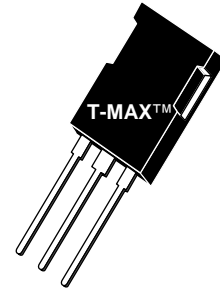


**POWER MOS V®**
**FREDFET**

Power MOS V® is a new generation of high voltage N-Channel enhancement mode power MOSFETs. This new technology minimizes the JFET effect, increases packing density and reduces the on-resistance. Power MOS V® also achieves faster switching speeds through optimized gate layout.



- **Fast Recovery Body Diode**
- **100% Avalanche Tested**
- **Lower Leakage**
- **Faster Switching**
- **Popular T-MAX™ Package**

**MAXIMUM RATINGS**

 All Ratings:  $T_C = 25^\circ\text{C}$  unless otherwise specified.

Symbol	Parameter	APT50M80B2VFR	UNIT
$V_{DSS}$	Drain-Source Voltage	500	Volts
$I_D$	Continuous Drain Current @ $T_C = 25^\circ\text{C}$	58	Amps
$I_{DM}$	Pulsed Drain Current <sup>①</sup>	232	
$V_{GS}$	Gate-Source Voltage Continuous	$\pm 30$	Volts
$V_{GSM}$	Gate-Source Voltage Transient	$\pm 40$	
$P_D$	Total Power Dissipation @ $T_C = 25^\circ\text{C}$	625	Watts
	Linear Derating Factor	5.0	W/ $^\circ\text{C}$
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to 150	$^\circ\text{C}$
$T_L$	Lead Temperature: 0.063" from Case for 10 Sec.	300	
$I_{AR}$	Avalanche Current <sup>①</sup> (Repetitive and Non-Repetitive)	58	Amps
$E_{AR}$	Repetitive Avalanche Energy <sup>①</sup>	50	mJ
$E_{AS}$	Single Pulse Avalanche Energy <sup>④</sup>	3000	

**STATIC ELECTRICAL CHARACTERISTICS**

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
$BV_{DSS}$	Drain-Source Breakdown Voltage ( $V_{GS} = 0V, I_D = 250\mu\text{A}$ )	500			Volts
$I_{D(on)}$	On State Drain Current <sup>②</sup> ( $V_{DS} > I_{D(on)} \times R_{DS(on)}$ Max, $V_{GS} = 10V$ )	58			Amps
$R_{DS(on)}$	Drain-Source On-State Resistance <sup>②</sup> ( $V_{GS} = 10V, 0.5 I_{D[Cont.]}$ )			0.080	Ohms
$I_{DSS}$	Zero Gate Voltage Drain Current ( $V_{DS} = V_{DSS}, V_{GS} = 0V$ )			250	$\mu\text{A}$
	Zero Gate Voltage Drain Current ( $V_{DS} = 0.8 V_{DSS}, V_{GS} = 0V, T_C = 125^\circ\text{C}$ )			1000	
$I_{GSS}$	Gate-Source Leakage Current ( $V_{GS} = \pm 30V, V_{DS} = 0V$ )			$\pm 100$	nA
$V_{GS(th)}$	Gate Threshold Voltage ( $V_{DS} = V_{GS}, I_D = 2.5\text{mA}$ )	2		4	Volts

 **CAUTION:** These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

APT Website - <http://www.advancedpower.com>

**DYNAMIC CHARACTERISTICS**

**APT50M80B2VFR**

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C <sub>ISS</sub>	Input Capacitance	V <sub>GS</sub> = 0V		8630		pF
C <sub>OSS</sub>	Output Capacitance	V <sub>DS</sub> = 25V		1160		
C <sub>RSS</sub>	Reverse Transfer Capacitance	f = 1 MHz		440		
Q <sub>g</sub>	Total Gate Charge <sup>③</sup>	V <sub>GS</sub> = 10V		360		nC
Q <sub>GS</sub>	Gate-Source Charge	V <sub>DD</sub> = 0.5 V <sub>DSS</sub>		57		
Q <sub>gd</sub>	Gate-Drain ("Miller") Charge	I <sub>D</sub> = I <sub>D</sub> [Cont.] @ 25°C		151		
t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>GS</sub> = 15V		16		ns
t <sub>r</sub>	Rise Time	V <sub>DD</sub> = 0.5 V <sub>DSS</sub>		18		
t <sub>d(off)</sub>	Turn-off Delay Time	I <sub>D</sub> = I <sub>D</sub> [Cont.] @ 25°C		60		
t <sub>f</sub>	Fall Time	R <sub>G</sub> = 0.6Ω		6		

**SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS**

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
I <sub>S</sub>	Continuous Source Current (Body Diode)		58		Amps
I <sub>SM</sub>	Pulsed Source Current <sup>①</sup> (Body Diode)		232		
V <sub>SD</sub>	Diode Forward Voltage <sup>②</sup> (V <sub>GS</sub> = 0V, I <sub>S</sub> = -I <sub>D</sub> [Cont.])			1.3	Volts
dv/dt	Peak Diode Recovery dv/dt <sup>⑤</sup>			5	V/ns
t <sub>rr</sub>	Reverse Recovery Time (I <sub>S</sub> = -I <sub>D</sub> [Cont.], di/dt = 100A/μs)	T <sub>j</sub> = 25°C		270	ns
		T <sub>j</sub> = 125°C		540	
Q <sub>rr</sub>	Reverse Recovery Charge (I <sub>S</sub> = -I <sub>D</sub> [Cont.], di/dt = 100A/μs)	T <sub>j</sub> = 25°C		1.8	μC
		T <sub>j</sub> = 125°C		6.2	
I <sub>RRM</sub>	Peak Recovery Current (I <sub>S</sub> = -I <sub>D</sub> [Cont.], di/dt = 100A/μs)	T <sub>j</sub> = 25°C		16	Amps
		T <sub>j</sub> = 125°C		29	

**THERMAL CHARACTERISTICS**

Symbol	Characteristic	MIN	TYP	MAX	UNIT
R <sub>θJC</sub>	Junction to Case			0.20	°C/W
R <sub>θJA</sub>	Junction to Ambient			40	

① Repetitive Rating: Pulse width limited by maximum junction temperature.

② Pulse Test: Pulse width < 380 μs, Duty Cycle < 2%

③ See MIL-STD-750 Method 3471

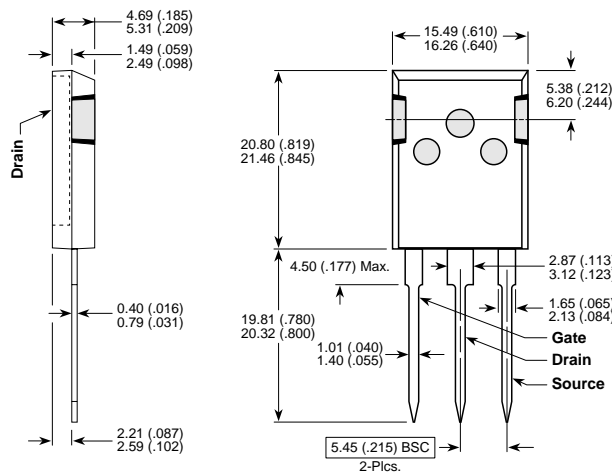
④ Starting T<sub>j</sub> = +25°C, L = 1.78mH, R<sub>G</sub> = 25Ω, Peak I<sub>L</sub> = 58A

⑤ I<sub>S</sub> = -I<sub>D</sub> [Cont.], di/dt = 100A/μs, V<sub>DD</sub> = V<sub>DSS</sub>, T<sub>j</sub> = 150°C, R<sub>G</sub> = 2.0Ω, V<sub>R</sub> = 200V.

**APT Reserves the right to change, without notice, the specifications and information contained herein.**

These dimensions are equal to the TO-247AD without mounting hole.

**T-MAX™ Package Outline**



Dimensions in Millimeters and (Inches)

APT's devices are covered by one or more of the following U.S. patents: 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336  
5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058